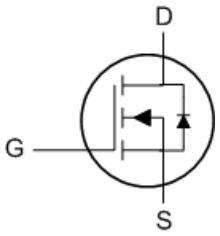
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

SOT23 Pin Configuration

Product Summary

BVDSS	RDSON	ID
60V	70 mΩ	3A



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	3.0	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	1.8	A
I_{DM}	Pulsed Drain Current[2]	9.2	A
P_D@T_A=25℃	Total Power Dissipation[3]	1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	125	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	80	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.054	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=2A	---	69	90	mΩ
		V_{GS}=4.5V , I_D=1A	---	81	110	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.8	---	1.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.96	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=2A	---	13	---	S
Q_g	Total Gate Charge (4.5V)	V_{DS}=48V , V_{GS}=4.5V , I_D=2A	---	5	7.0	nC
Q_{gs}	Gate-Source Charge		---	1.68	2.4	
Q_{gd}	Gate-Drain Charge		---	1.9	2.7	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=2A	---	1.6	3.2	ns
T_r	Rise Time		---	7.2	13	
$T_{d(off)}$	Turn-Off Delay Time		---	25	50	
T_f	Fall Time		---	14.4	28.8	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	280	---	pF
C_{oss}	Output Capacitance		---	38	53	
C_{rss}	Reverse Transfer Capacitance		---	25	35	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	2.3	A
I_{SM}	Pulsed Source Current[2,4]		---	---	9.2	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=2A , dI/dt=100A/μs , T_J=25℃	---	9.7	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.8	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature.
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

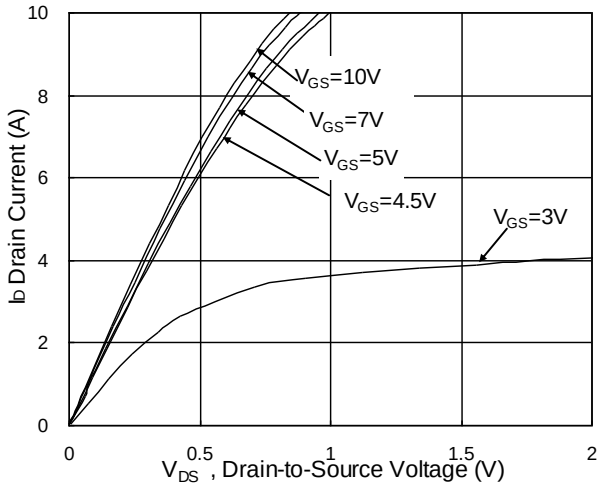


Fig.1 Typical Output Characteristics

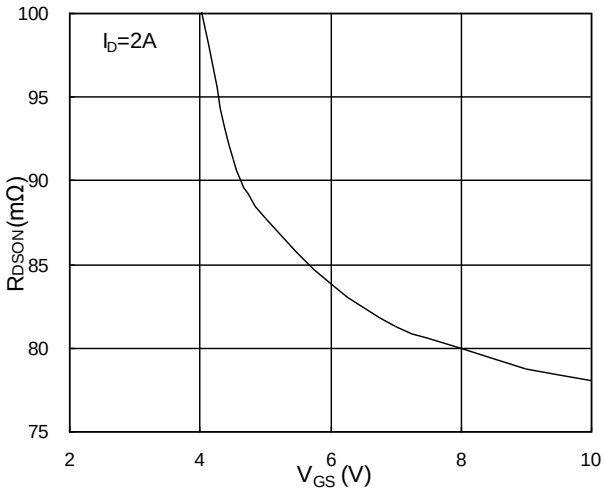


Fig.2 On-Resistance v.s Gate-Source

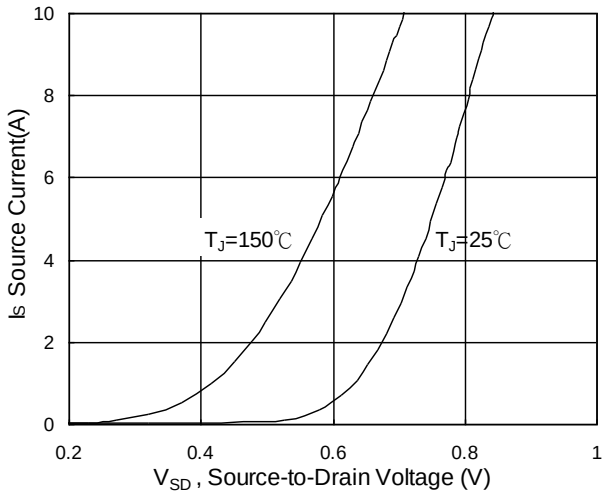


Fig.3 Forward Characteristics of Reverse

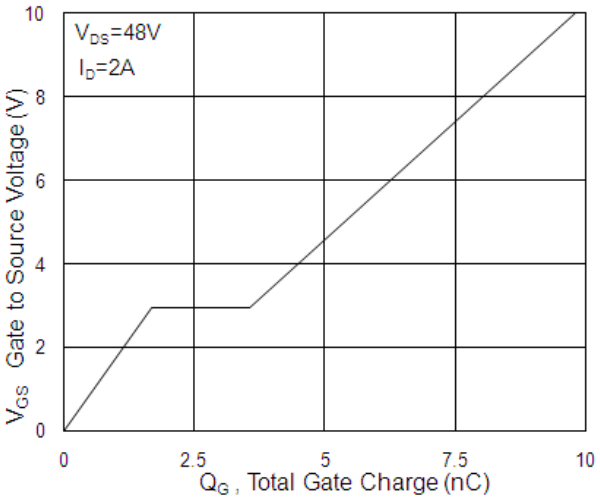


Fig.4 Gate-Charge Characteristics

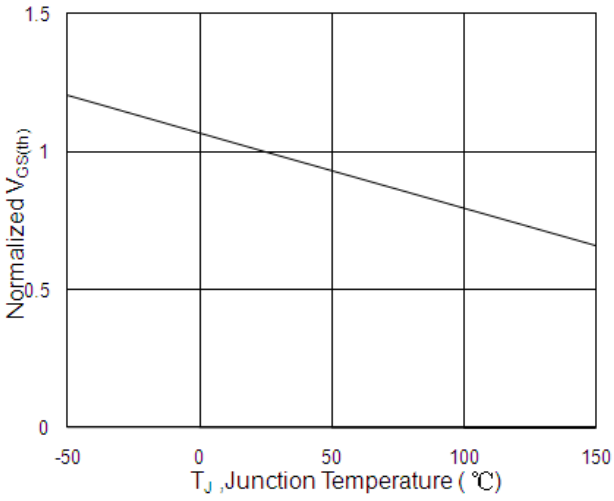


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

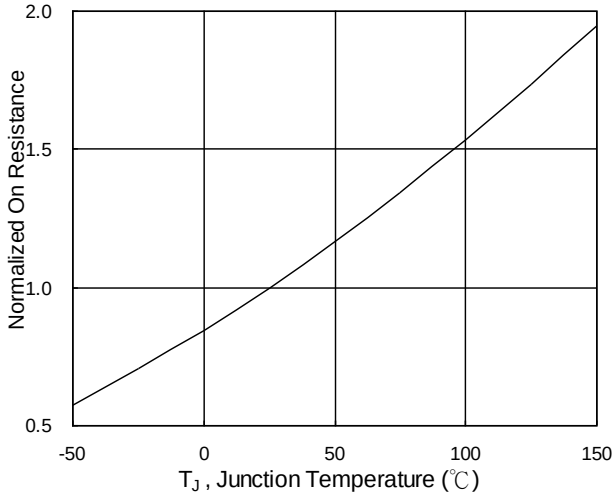


Fig.6 Normalized R_{DSON} v.s T_J

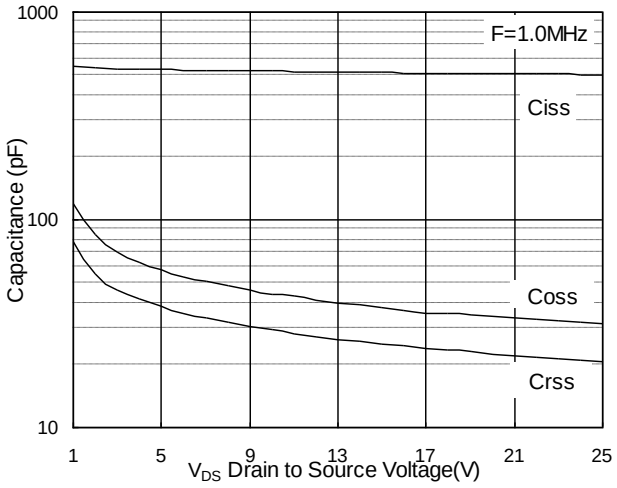


Fig.7 Capacitance

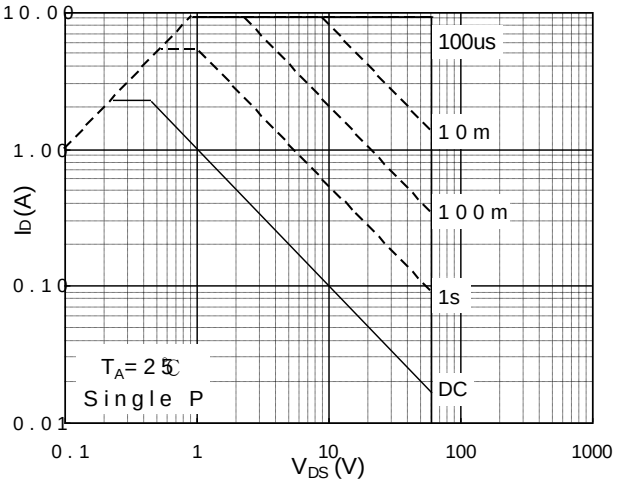


Fig.8 Safe Operating Area

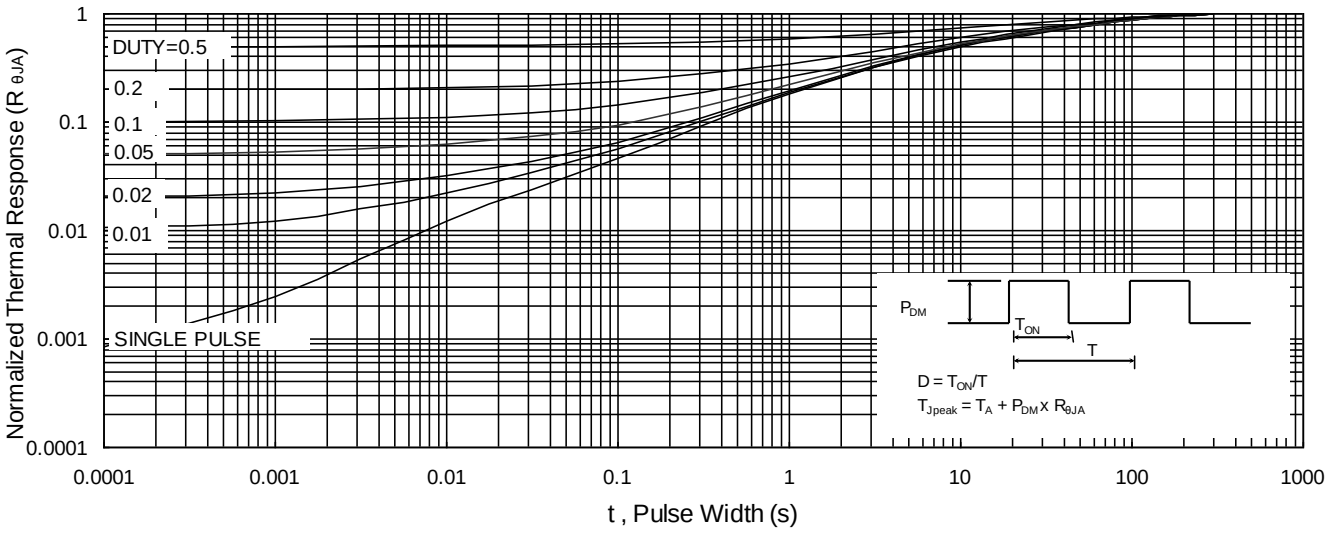


Fig.9 Normalized Maximum Transient Thermal Impedance

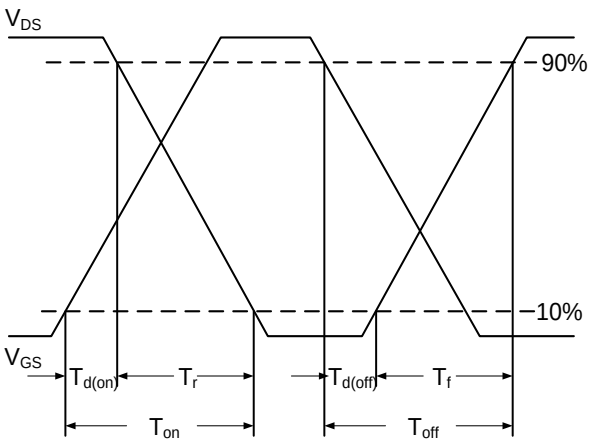


Fig.10 Switching Time Waveform

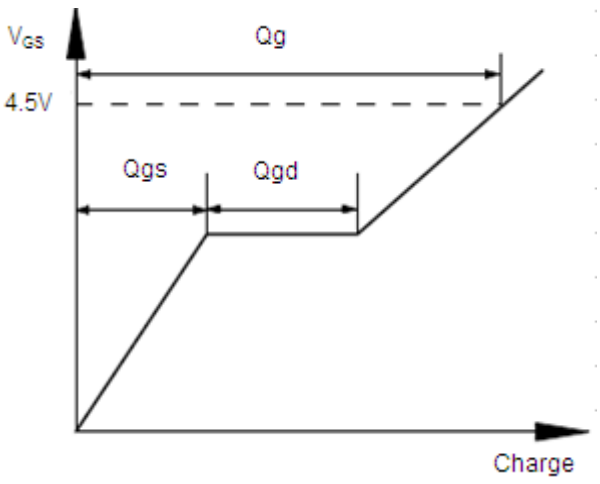


Fig.11 Gate Charge Waveform